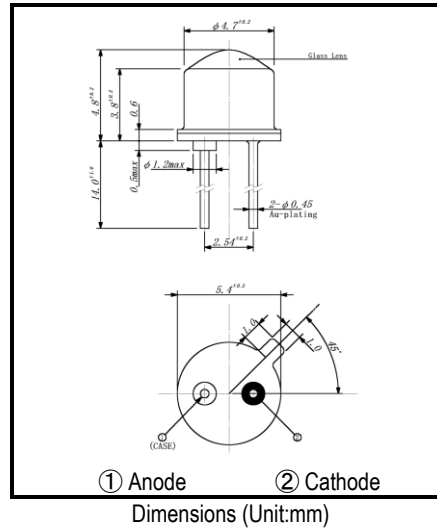


VS637NJ2

Infrared Emitting Diode



- FEATURES**
- Parallel Rays (Excellent)
 - High-output Power
 - High Reliability in Demanding Environments

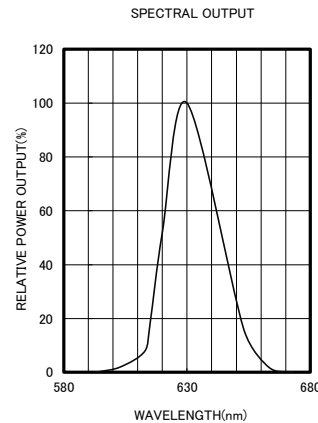
- APPLICATIONS**
- Optical Switches
 - Linear & Rotary Encoder

1. ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

ITEM	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	50	mA
Forward Current (Pulse)*1	IFP	0.3	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	120	mW
Operating Temp.	Topr	-20 TO 80	°C
Storage Temp.	Tstg	-30 TO 100	°C
Junction Temp.	Tj	100	°C
Lead Soldering Temp.*2	Tls	260	°C

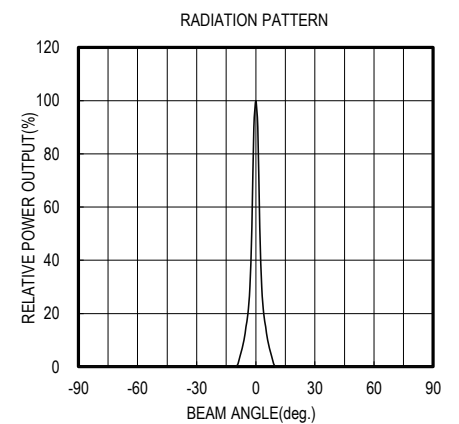
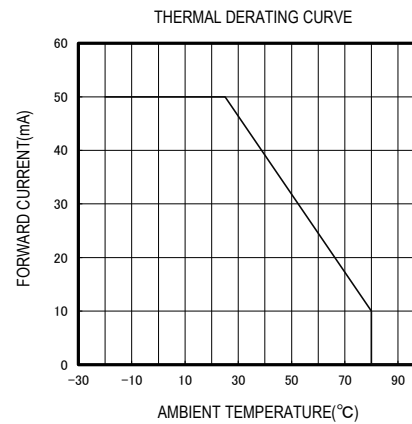
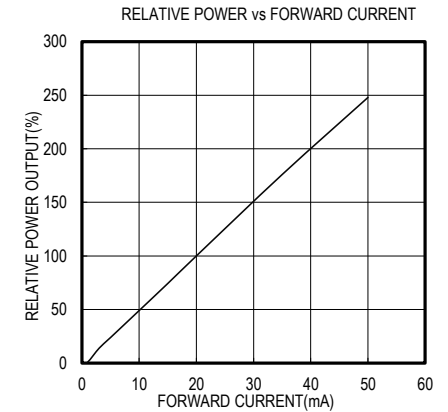
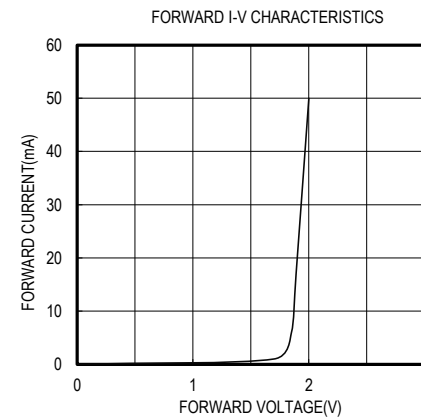
*1: Tw=10uS, T=1mS

*2: Time 5 Sec max, Position: Up to 3mm from the body



2. ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25°C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=20mA		4.0		mW
Forward Voltage	VF	IF=20mA		1.9	2.2	V
Reverse Current	IR	VR=5V			100	μA
Peak Wavelength	λ_p	IF=20mA		630		nm
Spectral Line Half Width	$\Delta \lambda$	IF=20mA		15		nm
Half Intensity Beam Angle	θ	IF=20mA		±2.5		deg.



OPTRANS

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